NPN Silicon Transistor







Pin Configuration:

- 1. Base
- 2. Emitter
- 3. Collector

Feature:

NPN Silicon Planar Epitaxial RF Transistor

Absolute Maximum Ratings

Description	Symbol	BC640	Unit
Collector Emitter Voltage	V _{CEO}	25	
Collector Base Voltage	V _{CBO}	40	V
Emitter-Base Voltage	V _{EBO}	4	
Collector Current Continuous	I _c	100	А
Power Dissipation at T _a = 25°C Derate Above 25°C	Б	350 2.8	mW mW/°C
Power Dissipation at T _C = 25°C Derate Above 25°C	P _D	1 8	W mW/°C
Operating and Storage Junction Temperature Range	T_{j},T_{stg}	-55 to +150	°C

Thermal Resistance

From Junction to Case	R _{th (j-c)}	125	°C/W
Junction to Ambient in Free Air	R _{th (j-a)}	357	C/VV

Electrical Characteristics ($T_a = 25$ °C unless otherwise specified)

Description	Symbol	Test Condition	Min.	Тур.	Max.	Units
Collector Emitter Voltage	V _{CEO} *	$I_{\rm C} = 1 \text{mA}, I_{\rm B} = 0$	25	-	-	٧
Collector Base Voltage	V _{CBO}	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	40	-	-	
Emitter-Base Voltage	V _{EBO}	$I_{E} = 10 \mu A, I_{C} = 0$	4	-	-	
Collector Cut off Current	I _{CBO}	V _{CB} = 20V, I _E = 0	-	-	100	nA

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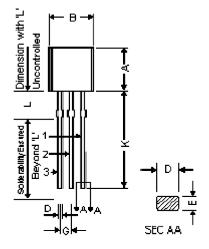


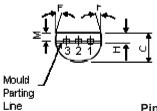
Electrical Characteristics ($T_a = 25$ °C unless otherwise specified)

Description	Symbol	Test Condition	Min.	Тур.	Max.	Units
DC Current Gain	h _{FE}	I _C = 7mA, V _{CE} = 10V	40	-	-	-
Base Emitter On Voltage	V _{BE (on)}	I _C = 7mA, V _{CE} = 10V	-	-	0.9	V

Dynamic Characteristics

Transistors Frequency	f _T	$I_C = 5mA, V_{CE} = 10V,$ f = 100MHz	400	-	-	MHz
Common Emitter Feedback Capacitance	C _{re}	$V_{CB} = 10V, I_{E} = 0,$ f = 1MHz	-	-	0.35	pF
Noise Figure	NF	$I_{C} = 4\text{mA}, V_{CE} = 10\text{V}, R_{S} = 50\Omega, f = 35\text{MHz}$	-	2.5	-	dB





Dimensions	Min. Max.		
А	4.32	5.33	
В	4.45	5.2	
С	3.18	4.19	
D	0.41	0.55	
E	0.35	0.5	
F	5°		
G	1.14	1.4	
Н	1.2	1.4	
K	12.7	-	
L	1.982	2.082	
M	1.03	1.2	

Dimensions: Millimetres

Pin Configuration:

- 1. Base
- 2. Emitter
- 3. Collector

Part Number Table

Description	Part Number
Transistor, NPN, TO-92	BF199

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